

FORM PTO-1449 (Rev. 2-32)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)	ATTY. DOCKET NO. TI-33969	SERIAL NO. <del>New</del> 10/618473
	APPLICANT: Xiaowei Deng, et al.	
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## U.S. PATENT DOCUMENTS

[illegible]

**FOREIGN PATENT DOCUMENTS**


**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

VTN		Koji Nii, et al., "A 90 nm Low Power 32K-Byte Embedded SRAM with Gate Leakage Suppression Circuit for Mobile Applications", Symposium on VLSI Circuits, 2003.

EXAMINER <i>W. H. Nelson</i>	Date: <i>8/7/04</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.